March 1999 ADVANCE INFORMATION



FDD5670 60V N-Channel PowerTrench[™] MOSFET

General Description

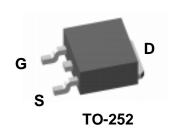
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

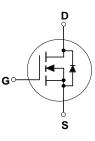
These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable ${\sf R}_{\sf DS(ON)}$ specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

Features

- 48 A, 60 V. $R_{DS(ON)} = 0.015 \Omega @ V_{GS} = 10 V$ $R_{DS(ON)} = 0.018 \Omega @ V_{GS} = 6 V.$
- Low gate charge.
- Fast switching speed.
- High performance trench technology for extremely low $\rm R_{\rm DS(ON)}.$





Absolute Maximum Ratings T_{c=25°C} unless otherwise noted

Symbol	Parameter		Ratings	Units V	
V _{DSS}	Drain-Source Voltage		60		
V _{GSS}	Gate-Source Voltage		±20	V	
I _D	Maximum Drain Current -Continuous	(Note 1)	48	A	
		(Note 1a)	10		
	Maximum Drain Current -Pulsed		100		
PD	Maximum Power Dissipation @ $T_c = 25^{\circ}C$	(Note 1)	70	W	
	$T_A = 25^{\circ}C$	(Note 1a)	2.8		
	$T_A = 25^{\circ}C$	(Note 1b)	1.3		
T _J , T _{stg}	Operating and Storage Junction Temperature	Range	-55 to +150	°C	

Thermal Characteristics

$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to- Case	(Note 1)	1.8	°C/W
$R_{ heta JA}$	Thermal Resistance, Junction-to- Ambient	(Note 1b)	96	°C/W

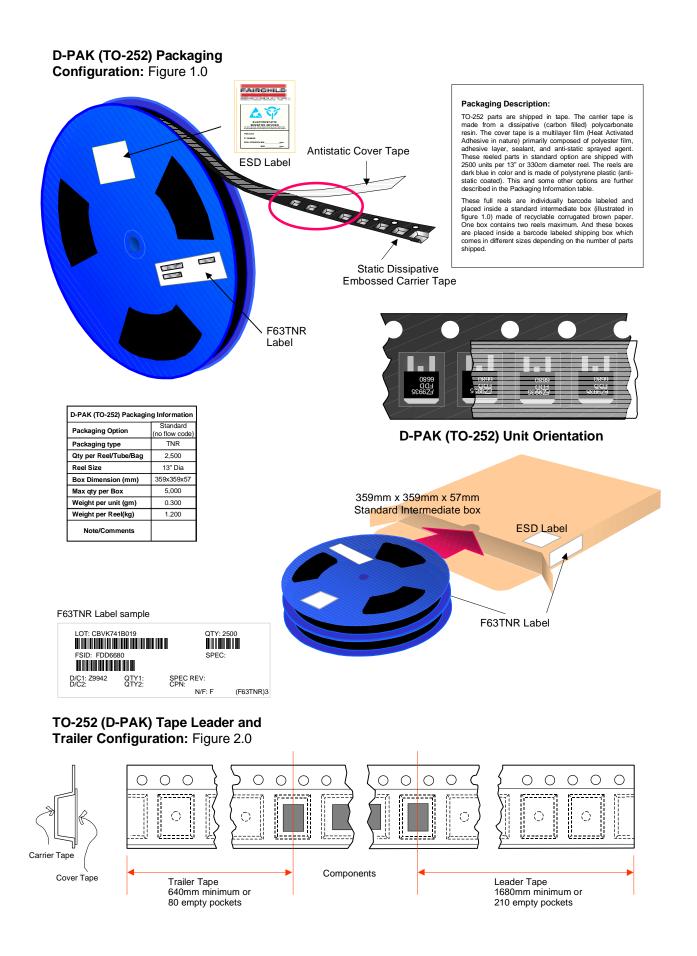
Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity	
FDD5670	FDD5670	13"	16mm	2500	

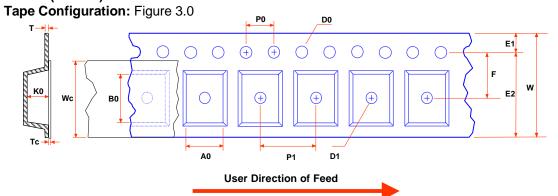
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Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
DEE CH	ARACTERISTICS					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$	60			V
DSS	Zero Gate Voltage Drain Current	$V_{DS} = 48 V, V_{GS} = 0 V$			1	μA
GSSF	Gate-Body Leakage, Forward	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
GSSR	Gate-Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$			-100	nA
ON CHA	RACTERISTICS (Note 2)					
V _{GS(TH)}	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	2		4	V
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$ $V_{GS} = 6 \text{ V}, I_D = 9 \text{ A}$			0.015 0.018	Ω
DRAIN-S	SOURCE DIODE CHARACT	ERISTICS AND MAXIMUM	I RATINO	S		
s	Maximum Continuous Drain-Source				48	А
/ _{SD}	Drain-Source Diode Forward	V _{GS} = 0 V, I _S = 2.4 A			1.2	V
	a) $R_{\theta JA} = 45^{\circ}C/W$ whe a 1 in ² pad of 2oz copp		R _{0JA} =96 ^o C/W 1 0.076 in ² pad of 2			
	0011					
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FDD5670



D-PAK (TO-252) Embossed Carrier



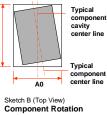
	Dimensions are in millimeter													
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	К0	т	Wc	Тс
TO252 (24mm)	6.90 +/-0.10	10.50 +/-0.10	16.0 +/-0.3	1.55 +/-0.05	1.5 +/-0.10	1.75 +/-0.10	14.25 min	7.50 +/-0.10	8.0 +/-0.1	4.0 +/-0.1	2.65 +/-0.10	0.30 +/-0.05	13.0 +/-0.3	0.06 +/-0.02

В0

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View) Component Rotation

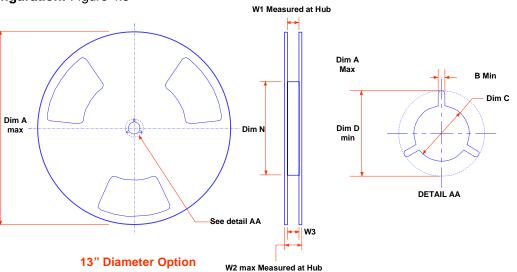


10 deg maximum



Sketch C (Top View) Component lateral movement

D-PAK (TO-252) Reel Configuration: Figure 4.0



Dimensions are in inches and millimeters Reel Option Dim W2 Dim W3 (LSL-USL) Tape Size Dim A Dim B Dim C Dim D Dim N Dim W1 13.00 0.059 1.5 512 +0.020/-0.008 13 +0.5/-0.2 0.795 20.2 4.00 100 0.646 +0.078/-0.000 16.4 +2/0 0.882 0.626 - 0.764 15.9 - 19.4 164mm 13" Dia 330 22.4

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